## 20-Output DB2000Q Buffer with Ultra Low Additive Jitter

## Features

- Fully Compliant with Intel DB2000Q Specification
- 20 Low-Power Push-Pull HCSL PCle Outputs
- Ultra-low additive jitter: 20fs maximum
- Supports clock frequencies from 0 to 250 MHz
- Supports 3.3V power supplies
- Embedded Low Drop Out (LDO) Voltage regulator provides superior Power Supply Noise Rejection
- Maximum output to output skew of 50 ps
- SMBus Interface
- Eight OE pins
- Embedded series terminations adjusted for $85 \Omega$ differential transmission line
- Transparent for Spread-Spectrum Clock


## Ordering Information

```
ZL40292LDG1 72 pin QFN Trays
ZL40292LDF1 72 pin QFN Tape and Reel
    Package size: 10\times10 mm
    -40}\mp@subsup{0}{}{\circ}\textrm{C}\mathrm{ to +85 %
```


## Applications

- PCI Express generation $1 / 2 / 3 / 4 / 5$ clock distribution
- Intel QPI
- Servers
- Storage and Data Centers
- Switches and Routers


Figure 1. Functional Block Diagram

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## Microsemi

## Pin Diagram

The device is packaged in a $10 \times 10 \mathrm{~mm} 72-\mathrm{pin}$ QFN.


Figure 2. Pin Diagram

## Pin Descriptions

The I/O column uses the following symbols: I - input, $\mathrm{I}_{\mathrm{PU}}$ - input with $120 \mathrm{k} \Omega$ internal pull-up resistor, $\mathrm{I}_{\mathrm{PD}}$ - input with $300 \mathrm{k} \Omega$ internal pull-down resistor, O - output, I/O - Input/Output Drain pin, NC-No connect pin, P - power supply pin, . Itri - Tri-level input pin biased to VDD/2 by internal $120 \mathrm{k} \Omega$ pull-up and $120 \mathrm{k} \Omega$ pull-down resistor.

Table 1Pin Descriptions

| \# | Name | I/O | Description |
| :---: | :---: | :---: | :---: |
| Input Reference |  |  |  |
| $\begin{gathered} 9 \\ 10 \end{gathered}$ | CLK_IN CLK_IN\# | 1 | Input Differential or Single Ended Reference <br> Input frequency range 0 Hz to 250 MHz . |
| Output Clocks |  |  |  |
| $\begin{aligned} & 19 \\ & 20 \\ & 22 \\ & 23 \\ & 24 \\ & 25 \\ & 27 \\ & 28 \\ & 29 \\ & 30 \\ & 32 \\ & 33 \\ & 35 \\ & 36 \\ & 38 \\ & 39 \\ & 41 \\ & 42 \\ & 46 \\ & 47 \\ & 49 \\ & 50 \\ & 52 \\ & 53 \\ & 55 \\ & 56 \\ & 59 \\ & 60 \\ & 61 \\ & 62 \\ & 64 \\ & 65 \end{aligned}$ | CK_0 CK 0 O <br> CK_1 <br> CK_1\# <br> CK_2 <br> CK_2\# <br> CK_3 <br> CK_3\# <br> CK_4 <br> CK_5 <br> CK_5\# <br> CK_6 <br> CK_6\# <br> CK_7 <br> CK_8 <br> CK_8\# <br> CK_9 <br> CK_9\# <br> CK_10 <br> CK_10\# <br> CK_11\# <br> CK_12 <br> CK_12\# <br> CK_13 <br> CK_13\# <br> CK_14\# <br> CK_15 <br> CK_15\# | O | Ultra-Low Additive Jitter Differential Outputs 0 to 19 Output frequency range 0 to 250 MHz |


| $\begin{aligned} & 66 \\ & 67 \\ & 69 \\ & 70 \\ & 71 \\ & 72 \\ & 17 \\ & 18 \end{aligned}$ | $\begin{gathered} \text { CK_16 } \\ \text { CK_16\# } \\ \text { CK_17 } \\ \text { CK_17\# } \\ \text { CK_18 } \\ \text { CK_18\# } \\ \text { CK_19\# } \\ \text { CK_19 } \end{gathered}$ |  |  |  |
| :---: | :---: | :---: | :---: | :---: |
| Hardware Control |  |  |  |  |
| $\begin{aligned} & 34 \\ & 37 \\ & 40 \\ & 43 \\ & 48 \\ & 51 \\ & 54 \\ & 57 \end{aligned}$ | OE 5\# <br> OE 6\# <br> OE_7\# <br> OE_8\# <br> OE_9\# <br> OE_10\# <br> OE_11\# <br> OE_12\# | $I_{P D}$ | Output Enable. Logic level on these pins enables/disables the corresponding output. |  |
|  |  |  | OE_n\# | CK_n/n\# |
|  |  |  | 0 | Active |
|  |  |  | 1 | Low/Low both pulled low by $42.5 \Omega$ resistor |
| 6 | PWRGD/PWRDN\# | 1 | Power u |  |
| 3 | R_COMP | 1 | Not used |  |

## SMBus Control

| 13 | SCL | I | SMBus slave clock input |
| :---: | :---: | :---: | :--- |
| 12 | SDA | I/O | Input/Open drain SMBus data |
| 11 <br> 14 | SA_0 $^{\text {SA_1 }}$ | ITRI | Tri level address selection inputs |

Power and Ground

| 1 | VDD | P | Positive Supply Voltage. Connect to 3.3V supply. |
| :---: | :--- | :--- | :--- |
| 4 |  |  |  |
| 21 |  |  |  |
| 31 |  |  |  |
| 45 |  | P | Positive Analog Supply Voltage Connect 3.3V power supply. |
| 58 |  | P | Ground Connect to ground |
| 68 | VDD_A |  |  |
| 8 | GND |  | Analog Ground. Connect to ground |
| 26 |  |  |  |
| 44 | GND_A |  |  |
| 7 |  |  |  |


| E-Pad | GND | P | Ground. Connect to ground |
| :---: | :---: | :---: | :--- |
| No Connect Pins |  |  |  |
| 5 | N/C |  | No Connect. These pins are not connected to the die. Leave them open. <br> One of these pins might be used for future modifications of DB2000Q spec. The <br> current DB2000Q v1.0 standard calls for RFU (Reserved for Future Upgrades) pin <br> but does not assign it to any pin number. |

## Functional Description

The ZL40292 is an ultra-low additive jitter, low power 1 to 20 fanout buffer which is fully compliant with Intel DB2000Q Standard.
The device operates from $3.3 \mathrm{~V}+/-5 \%$ supply as per Intel spec. Its operation is guaranteed over the industrial temperature range $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$.

## Clock Inputs

The following blocks diagram shows how to terminate different signals fed to the ZL40292 inputs.
The device input can be fed with transmission lines of any impedance. Examples below show only $50 \Omega$ single ended, $85 \Omega$ differential and $100 \Omega$ differential which are the most common ones in practice. Figure 3 and Figure 4 show how to terminate the input when driven from a push-pull and traditional HCSL drivers respectively.
Figure 5 shows how to terminate a single ended output such as LVCMOS. This example assumes $50 \Omega$ transmission line which is the most common for single ended CMOS signaling. Resistors R1 and R2 are chosen to provide $50 \Omega$ termination and proper biasing and Ro + Rs ideally should be $50 \Omega$ so that the transmission line is terminated at both ends with its characteristic impedance. If the driving strength of the output driver is not sufficient to drive low impedance, the value of series resistor $R_{s}$ should be increased. This will reduce the voltage swing at the input but this should be fine as long as the input voltage swing requirement is not violated (Figure 5). The source resistors of Rs = $270 \Omega$ could be used for standard LVCMOS driver. This will provide 516 mV of voltage swing for 3.3 V LVCMOS driver with load current of $(3.3 \mathrm{~V} / 2) *(1 /(270 \Omega+50 \Omega))=5.16 \mathrm{~mA}$.
For optimum performance both differential input pins ( $\_$p and _n) need to be DC biased to the same voltage. Hence, the ratio $R 1 / R 2$ should be equal to the ratio $R 3 / R 4$.


Figure 3. Input driven by a push-pull differential output


Figure 4. Input driven by an HCSL output


Figure 5. Input driven by a single ended output

## Clock Outputs

Differential outputs have embedded termination resistors as shown in Figure 6. This provides significant saving relative to traditional current based HCSL outputs which require four resistors per differential pair (80 resistors for 20 outputs).

Embedded series termination resistors are matched for $85 \Omega$ differential transmission line.


Figure 6. Terminating differential outputs.

## Termination of unused outputs

Unused outputs should be left unconnected.

## Power Supply Filtering

Each power pin (VDDA and VDD) should be decoupled with $0.1 \mu \mathrm{~F}$ capacitor with minimum equivalent series resistance (ESR) and minimum series inductance (ESL). For example, 0402 X5R Ceramic Capacitors with 6.3 V minimum rating could be used. These capacitors should be placed as close as possible to the power pins. To reduce the power noise from adjacent digital components on the board each power supply could be further insulated with low DC resistance ferrite bead with two capacitors. The ferrite bead will also insulate adjacent component from the noise generated from the device. Following figure shows recommended decoupling.


Figure 7. Power Supply Filtering

## OE\# and Output Enables (Control Register)

Each output can be individually enabled or disabled by SMBus control register bits or via OE\# pin. The OE\# pins are asynchronous asserted-low signals. The Output Enable bits in the SMBus registers are active high and are set to enable by default.
OE\# pins are mapped to CK[12:5] outputs.
Note that the logic level for assertion or de-assertion is different in software than it is on hardware. This follows hardware default nomenclature for communication channels (e.g., output is enabled if OE\# pin is pulled low) and still maintains software programming logic (e.g., output is enabled if OE register is true).

Refer to Table 2 for the truth table for enabling and disabling outputs via hardware and software. Note that both the control register bit must be a ' 1 ' AND the OE\# pin must be a ' 0 ' for the output to be active.

Table 2 OE Functionality

| Inputs |  | OE\# Hardware Pins and <br> Control Register Bits |  |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: |
| PWRGD/ <br> PWRDN\# | CK_IN/ <br> CK_IN\# | SMBUS <br> Enable Bit | OE\# <br> Pin | CK/CK\# <br> [12:5] | CK/CK\# <br> [4:0] and [19:13] |
| 0 | $X$ | $X$ | $X$ | 0 | 0 |
| 1 | Running | 0 | $X$ | 0 | 0 |
|  |  | 1 | 0 | Running | Running |
|  |  | 1 | 1 | 0 | Running |

## OE\# Assertion (Transition from ' 1 ' to ' 0 ')

All differential outputs that were disabled are to resume normal operation in a glitch free manner. The latency from the assertion to active outputs is $0-10 \mathrm{CK}$ clock periods.

## OE\# De-Assertion (Transition from '0' to '1')

The impact of de-asserting OE\# is each corresponding output will transition from normal operation to disabled in a glitch free manner. A minimum of four valid clocks will be provided after the de-assertion of OE\#. The maximum latency from the de-assertion to disabled outputs is 10 CK clock periods.

## PWRGD / PWRDN\#

PWRGD is asserted high and de-asserted low. De-assertion of PWRGD (pulling the signal low) is equivalent to indicating a powerdown condition. PWRGD (assertion) is used by the ZL40292 to sample initial configurations such as SA selections.
After PWRGD has been asserted high for the first time, the pin becomes a PWRDN\# (Power Down) pin which is used to disable (drive low/low) all clocks cleanly and instruct the device to invoke power savings mode. PWRDN\# is a completely asynchronous active low input. When entering power savings mode, PWRDN\# should be asserted low prior to shutting off the input clock or power to ensure all clocks shut down in a glitch free manner. When PWRDN\# is de-asserted high, all clocks will start and stop without any abnormal behavior and will meet all AC and DC parameters.
The assertion and de-assertion of PWRDN\# is asynchronous.
Disabling of the CK_IN input clock prior to assertion of PWRDN\# is an undefined mode and not recommended. Operation in this mode may result in glitches.

Table 3 PWRGD / PWRDN\# Functionality

| PWRGD / PWRDN\# | CK | CK\# |
| :---: | :---: | :---: |
| 0 | LOW | LOW |
| 1 | Normal | Normal |

## PWRDN\# Assertion

When PWRDN\# is sampled low by two consecutive rising edges of CK\#, all differential outputs will be disabled on the next CK\# high to low transition.


Figure 8. PWRDN\# Assertion

## PWRGD Assertion

PWRGD to the clock buffer should not be asserted before $V_{D D}$ reaches $V_{D D \min }$. Prior to $V_{D D \min }$ it is recommended to hold PWRGD low (less than 0.5 V)


Figure 9. PWRGD and $\mathrm{V}_{\mathrm{DD}}$ Relationship diagram
The power-up latency Tstable is to be less than 1.8 ms . This is the time from the valid CLK_IN input clocks and the assertion of the PWRGD signal to the time that stable clocks are output from the buffer chip. All differential outputs stopped in a disabled condition resulting from power down must be driven high in less than $300 \mu \mathrm{~s}$ of PWRGD assertion to a voltage greater than 200 mV .


Figure 10. PWRGD Assertion

## Microsemi

Data Sheet
ZL40292

## Programming via SMBus

The address selection is done via SA 0 and SA 1 tri-level hardware pins, which select the appropriate address for the device. The two tri-level input pins that can configure the ZL40292 to nine different addresses (refer to Table 14 for VIL_Tri, VIm_Tri, VIH_Tri signal level).

Table 4 SMBus Address Table

| SA_1 | SA_0 | SMBus Address |
| :---: | :---: | :---: |
| L | L | D8 |
| L | $M$ | DA |
| L | H | DE |
| M | L | C2 |
| M | $M$ | C4 |
| $M$ | $H$ | C6 |
| $H$ | L | CA |
| $H$ | $M$ | CC |
| $H$ | $H$ | CE |

## SMBus Byte Read/Write

Reading or writing a register in a SMBus slave device in byte mode always involves specifying the register number.
Read. The standard byte read is as shown in Figure 11. It is an extension of the byte write. The write start condition is repeated then the slave device starts sending data and the master acknowledges it until the last byte is sent. The master terminates the transfer with a NAK then a stop condition. For byte operation, the $2^{*} 7^{\text {th }}$ bit of the command byte must be set. For block operations, the $2^{\star} 7^{\text {th }}$ bit must be reset. If the bit is not set, the next byte must be the byte transfer count.


Figure 11. SMBus Byte Read

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Write. Figure 12 illustrates a simple typical byte write. For byte operation the $2^{*} 7^{\text {th }}$ bit of the command byte must be set. For block operations, the $2^{*} 7^{\text {th }}$ bit must be reset. If the bit is not set the next byte must be the byte transfer count. The count can be between 1 and 32. It cannot be zero or exceed 32 .


Figure 12. SMBus Byte Write

## SMBus Block Read/Write

Read. After the slave address is sent with the r/w condition bit set, the command byte is sent with the MSB $=0$. The slave Ack's the register index in the command byte. The master sends a repeat start function. After the slave Ack's this the slave sends the number of bytes it wants to transfer ( $>0$ and <33). The master Ack's each byte except the last and sends a stop function.


Figure 13. SMBus Block Read

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Write. After the slave address is sent with the $\mathrm{r} / \mathrm{w}$ condition bit not set, the command byte is sent with the MSB $=0$. The lower seven bits indicate what register to start the transfer at. If the command byte is 00 h , the slave device will be compatible with existing block mode slave devices. The next byte of a write must be the count of bytes that the master will transfer to the slave device. The byte count must be greater than zero and less than 33. Following this byte are the data bytes to be transferred to the slave device. The slave device always acknowledges each byte received. The transfer is terminated after the slave sends the Ack and the master sends a stop function.


Figure 14. SMBus Block Write

## Register Map

Table 5 Byte 0: Output Enable

| Bit | Description | If Bit = 0 | If Bit = $\mathbf{1}$ | Type | Default | Output(s) Affected |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| 0 | Reserved |  |  |  | 0 |  |
| 1 | Reserved |  |  |  | 0 |  |
| 2 | Reserved |  |  |  | 0 |  |
| 3 | Output Enable CK 16 | LOW | Enable | RW | 1 | CK[16] |
| 4 | Output Enable CK 17 | LOW | Enable | RW | 1 | CK[17] |
| 5 | Output Enable CK 18 | LOW | Enable | RW | 1 | CK[18] |
| 6 | Output Enable CK 19 | LOW | Enable | RW | 1 | CK[19] |
| 7 | Reserved |  |  |  | 0 |  |

Table 6 Byte 1: Output Enable Control Register

| Bit | Description | If Bit = 0 | If Bit =1 | Type | Default | Output(s) <br> Affected |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| 0 | Output Enable CK 0 | LOW | Enabled | RW | 1 | CK[0] |
| 1 | Output Enable CK 1 | LOW | Enabled | RW | 1 | CK[1] |
| 2 | Output Enable CK 2 | LOW | Enabled | RW | 1 | CK[2] |
| 3 | Output Enable CK 3 | LOW | Enabled | RW | 1 | CK[3] |
| 4 | Output Enable CK 4 | LOW | Enabled | RW | 1 | CK[4] |
| 5 | Output Enable CK 5 | LOW | Enabled | RW | 1 | CK[5] |
| 6 | Output Enable CK 6 | LOW | Enabled | RW | 1 | CK[6] |
| 7 | Output Enable CK 7 | LOW | Enabled | RW | 1 | CK[7] |

Table 7 Byte 2: Output Enable Control Register

| Bit | Description | If Bit = 0 | If Bit =1 | Type | Default | Output(s) <br> Affected |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| 0 | Output Enable CK 8 | LOW | Enabled | RW | 1 | CK[8] |
| 1 | Output Enable CK 9 | LOW | Enabled | RW | 1 | CK[9] |
| 2 | Output Enable CK 10 | LOW | Enabled | RW | 1 | CK[10] |
| 3 | Output Enable CK 11 | LOW | Enabled | RW | 1 | CK[11] |
| 4 | Output Enable CK 12 | LOW | Enabled | RW | 1 | CK[12] |
| 5 | Output Enable CK 13 | LOW | Enabled | RW | 1 | CK[13] |
| 6 | Output Enable CK 14 | LOW | Enabled | RW | 1 | CK[14] |
| 7 | Output Enable CK 15 | LOW | Enabled | RW | 1 | CK[15] |

Table 8 Byte 3: OE\# Pin Realtime Readback Control Register

| Bit | Description | If Bit $=0$ | If Bit $=1$ | Type | Default | Output(s) <br> Affected |
| :---: | :---: | :---: | :---: | :---: | :--- | :---: |
| 0 | Realtime Readback of OE_5\# | OE_5\# Low | OE_5\# High | $R$ | Realtime | CK[5] |
| 1 | Realtime Readback of OE_6\# | OE_6\# Low | OE_6\# High | $R$ | Realtime | CK[6] |
| 2 | Realtime Readback of OE_7\# | OE_7\# Low | OE_7\# High | $R$ | Realtime | CK[7] |
| 3 | Realtime Readback of OE_8\# | OE_8\# Low | OE_8\# High | $R$ | Realtime | CK[8] |
| 4 | Realtime Readback of OE_9\# | OE_9\# Low | OE_9\# High | $R$ | Realtime | CK[9] |
| 5 | Realtime Readback of OE_10\# | OE_10\# Low | OE_10\# High | $R$ | Realtime | CK[10] |
| 6 | Realtime Readback of OE_11\# | OE_11\# Low | OE_11\# High | $R$ | Realtime | CK[11] |
| 7 | Realtime Readback of OE_12\# | OE_12\# Low | OE_12\# High | $R$ | Realtime | CK[12] |

Table 9 Byte 4: Reserved Control Register

| Bit | Description | If Bit = 0 | If Bit = 1 | Type | Default | Output(s) <br> Affected |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| 0 | Reserved |  |  |  | 0 |  |
| 1 | Reserved |  |  |  | 0 |  |
| 2 | Reserved |  |  |  | 0 |  |
| 3 | Reserved |  |  |  | 0 |  |
| 4 | Reserved |  |  |  | 0 |  |
| 5 | Reserved |  |  |  | 0 |  |
| 6 | Reserved |  |  |  | 0 |  |
| 7 | Reserved |  |  |  | 0 |  |

Table 10 Byte 5: Vendor/Revision Identification Control Register

| Bit | Description | If Bit <br> $=0$ | If Bit <br> $=1$ | Type | Default | Output(s) <br> Affected |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| 0 | Vendor ID Bit 0 |  |  | R | 1 |  |
| 1 | Vendor ID Bit 1 |  |  | R | 1 |  |
| 2 | Vendor ID Bit 2 |  |  | R | 0 |  |
| 3 | Vendor ID Bit 3 |  |  | R | 0 |  |
| 4 | Revision Code Bit 0 |  |  | R | 0 |  |
| 5 | Revision Code Bit 1 |  |  | R | 1 |  |
| 6 | Revision Code Bit 2 |  |  | R | 0 |  |
| 7 | Revision Code Bit 3 |  |  | R | 0 |  |

Table 11 Byte 6: Device ID Control Register

| Bit | Description | If Bit <br> $=0$ | If Bit <br> $=1$ | Type | Default | Output(s) <br> Affected |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| 0 | Device ID 0 |  |  | R | 0 |  |
| 1 | Device ID 1 |  |  | R | 0 |  |
| 2 | Device ID 2 |  |  | R | 1 |  |
| 3 | Device ID 3 |  |  | R | 1 |  |
| 4 | Device ID 4 |  |  | R | 1 |  |
| 5 | Device ID 5 |  |  | R | 0 |  |
| 6 | Device ID 6 |  |  | R | 1 |  |
| 7 | Device ID 7 (MSB) |  |  | R | 0 |  |

Table 12 Byte 7: Byte Count Register

| Bit | Description | $\begin{aligned} & \text { If Bit } \\ & =0 \end{aligned}$ | $\begin{aligned} & \text { If Bit } \\ & =1 \end{aligned}$ | Type | Default | Output(s) <br> Affected |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| 0 | BCO - Writing to this register configures how many bytes will be read back |  |  | RW | 0 |  |
| 1 | BC1 - Writing to this register configures how many bytes will be read back |  |  | RW | 0 |  |
| 2 | BC2 - Writing to this register configures how many bytes will be read back |  |  | RW | 0 |  |
| 3 | BC2 - Writing to this register configures how many bytes will be read back |  |  | RW | 1 |  |
| 4 | BC3-Writing to this register configures how many bytes will be read back |  |  | RW | 0 |  |
| 5 | BC4 - Writing to this register configures how many bytes will be read back |  |  | RW | 0 |  |
| 6 | Reserved |  |  |  | 0 |  |
| 7 | Reserved |  |  |  | 0 |  |

## AC and DC Electrical Characteristics

## Absolute Maximum Ratings

Table 13 Absolute Maximum Ratings*

|  | Parameter | Sym. | Min. | Max. | Units | Notes |
| :---: | :--- | :---: | :---: | :---: | :---: | :---: |
| 1 | 3.3 V Core Supply Voltage | $\mathrm{V}_{\mathrm{DD} \_\mathrm{A}}$ | - | 4.6 | V | 3 |
| 2 | 3.3 V I/O Supply Voltage | $\mathrm{V}_{\mathrm{DD}}$ | - | 4.6 | V | 3 |
| 5 | 3.3 V Input High Voltage | $\mathrm{V}_{I H}$ | - | 4.6 | V | 1,3 |
|  | 3.3 V Input Low Voltage | $\mathrm{V}_{\mathrm{IL}}$ | -0.5 | - | V | 3 |
|  | Storage Temperature | Ts | -65 | 150 | ${ }^{\circ} \mathrm{C}$ | 3 |
| 6 | Input ESD protection | $\mathrm{V}_{\mathrm{DD}-\mathrm{IN}}$ | 2000 |  | V | 2 |

* Exceeding these values may cause permanent damage
* Functional operation under these conditions is not implied
*Voltages are with respect to ground (GND) unless otherwise stated

1. Maximum VIH is not to exceed maximum VDD.
2. Human body model.
3. Consult manufacturer regarding extended operation in excess of normal DC operating parameters.

Microchip company
DC Electrical Specification
Table 14 DC Operating Characteristics*

|  | Parameter | Sym. | Min. | Typ. | Max. | Units | Notes |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| 1 | 3.3 V Core Supply Voltage | VDD_A | 3.135 | 3.3 | 3.465 | V |  |
| 2 | 3.3 V //O Supply Voltage | $V_{D D}$ | 3.135 | 3.3 | 3.465 | V |  |
| 3 | 3.3 V Input High Voltage | $\mathrm{V}_{\text {IH }}$ | 2.0 |  | VDD+0.3 | V |  |
| 4 | 3.3 V Input Low Voltage | VIL | VSS-0.3 |  | 0.8 | V |  |
| 5 | Input Leakage Current | ILL | -5 |  | +5 | $\mu \mathrm{A}$ |  |
| 6 | Input Low Voltage, 3-level CMOS Input | Vıз | VSS-0.3 |  | 0.9 | V |  |
| 7 | Input Midrange Voltage, 3-level CMOS Input | $\mathrm{V}_{\text {וм }}$ | 1.3 |  | 1.8 | V |  |
| 8 | Input High Voltage, 3-level CMOS Input | V нз | 2.4 |  | VDD | V |  |
| 9 | Input Capacitance | $\mathrm{C}_{\text {IN }}$ |  |  | 4.5 | pF | 1 |
| 10 | Output Capacitance | Cout |  |  | 4.5 | pF | 1 |
| 11 | Ambient Temperature | $\mathrm{T}_{\text {A }}$ | -40 |  | 85 | ${ }^{\circ} \mathrm{C}$ |  |

* Voltages are with respect to ground (GND) unless otherwise stated

1 For parasitic simulation use IBIS model.
Table 15 Differential DC Output Characteristics*

|  | Parameter | Sym. | Min. | Typ. | Max. | Units | Notes |
| :---: | :--- | :--- | :--- | :--- | :--- | :--- | :---: |
| 1 | Maximum Voltage (Overshoot) | Vovs |  |  | Vhigh +75 | mV | 1 |
| 2 | Maximum Voltage (Undershoot) | Vuds | Vhigh | 225 |  | Vlow -75 | mV |
| 3 | Voltage High | Vlow | 10 | 270 | mV | 1 |  |
| 4 | Voltage Low | Vcross absolute | 130 |  | 150 | mV | 1 |
| 5 | Absolute Crossing Point Voltages | Vcross relative |  | 200 | mV | 1 |  |
| 6 | Relative Crossing Point Voltages | DiffZ | $85-5 \%$ |  | 35 | mV | 1 |
| 7 | Output Buffer Differential Impedance | DiffZCrossing | $85-20 \%$ |  | $85+20 \%$ | $\Omega$ | 3 |
| 8 | Output Buffer Differential Impedance |  |  |  |  |  |  |

* Voltages are with respect to ground (GND) unless otherwise stated

Measured into DC testload, see Figure 15
2 Measured at VOL / VOH.
3 Measured during a transition


Eq1. $\quad R 1+(R 2| | 50 \Omega)=85 \Omega$
Eq2. $\quad((42.5 \Omega|\mid 85 \Omega)+R 1)|\mid R 2=50 \Omega$
$R 1=47.8 \Omega$, standard $1 \%$ value $R 1=47 \Omega$
$R 2=145.8 \Omega$, standard $1 \%$ value $R 2=147 \Omega$
Figure 15. DC Test Load (as per DB2000Q Specification)


Figure 16. Single-Ended Measurement Points for TRise and TFall


Figure 17. Single-Ended Measurement Points for Vovs, Vuds, Vrb


Figure 18. Differential (CK, CK\#) Measurement Points

AC Electrical Specification
Table 16 Power Noise Tolerance*

|  | VDD Electrical Noise Range | Symbol | Min. | Typ. | Max | Units | Notes |
| :--- | :--- | :---: | :---: | :---: | :---: | :---: | :---: |
| 1 | $f_{\text {NOISE }}=12 \mathrm{kHz}$ to 20 MHz | NVDD_MID | 100 |  |  | $\mathrm{mV}, \mathrm{p}-\mathrm{p}$ | $1,2,3$ |
| 2 | $\mathrm{f}_{\text {NOISE }}>20 \mathrm{MHz}$ | NVDD_HIGH | 50 |  |  | $\mathrm{mV}, \mathrm{p}-\mathrm{p}$ | $1,2,3$ |
| 3 | $\mathrm{f}_{\text {NOISE }}=12 \mathrm{kHz}$ to 20 MHz | NVDD_A_MID | 40 |  |  | $\mathrm{mV}, \mathrm{p}-\mathrm{p}$ | $1,2,3$ |
| 4 | $\mathrm{f}_{\text {NOISE }}>20 \mathrm{MHz}$ | NVDD_A_HIGH | 20 |  |  | $\mathrm{mV}, \mathrm{p}-\mathrm{p}$ | $1,2,3$ |

* The device meets all specification in the presence of noise specified in this table

1 Jitter and electrical characteristics are met with specified AC noise present on any of the power pins.
2 Over the specified frequency range, a single sinusoid tone should be assumed swept as the worst case.
3 Maximum measured frequency for VDD was 650 kHz and for VDD_A the maximum frequency was 900 kHz due to limitation of the test setup.
Table 17 Skew and Jitter

|  | Parameter | Symbol | Min. | Typ. | Max | Units | Notes |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| 1 | Input-to-Output Delay | $1 / O_{\text {deLay }}$ | 0.9 |  | 1.5 | ns | 1,3 |
| 2 | Output-to-Output Skew | $\mathrm{O} / \mathrm{O}_{\text {delay }}$ |  |  | 50 | ps | 1,2 |
| 3 | RMS Additive Jitter as per DB2000Q Spec | AJJMS |  | 15 | 20 | fs RMS | 1,2,4 |
| 4 | Peak-to-Peak Additive Jitter | $\mathrm{p}-\mathrm{pAJ} J_{\mathrm{RMS}}$ |  |  | 0.7 | ps | 1,2 |
| 5 | Additive Jitter as per PCle 1.0 (1.5MHz to 22 MHz ) | $\mathrm{T}_{\text {jPCle_1.0 }}$ |  | 0.7 | 0.8 | ps RMS | 1, 2 |
| 6 | Additive Jitter as per PCle 2.0 high band ( 1.5 MHz to 50 MHz ) | TjPCle_2.0_high |  | 75 | 94 | fs RMS | 1,2 |
| 7 | Additive Jitter as per PCle 2.0 low band ( 10 kHz to 1.5 MHz ) | T ${ }_{\text {jPCle_2.0_low }}$ |  | 20 | 28 | fs RMS | 1,2 |
| 8 | Additive Jitter as per PCle 2.0 mid band ( 5 MHz to 16 MHz ) | T jPCle _2.0_mid |  | 59 | 74 | fs RMS | 1,2 |
| 9 | Additive Jitter as per PCle 3.0 (PLL_BW = 2 to 5 MHz , CDR = 10 MHz ) | $\mathrm{T}_{\text {jPCle_3.0 }}$ |  | 19 | 24 | fs RMS | 1, 2 |
| 10 | Additive Jitter as per PCle 4.0 (PLL_BW = 2 to $5 \mathrm{MHz}, \mathrm{CDR}=$ 10 MHz ) | $\mathrm{T}_{\text {jPCle_4. }}$ |  | 19 | 24 | fs RMS | 1, 2 |
| 11 | Additive Jitter as per PCle 5.0 (PLL_BW $=0.5$ to 1.8 MHz , CDR for 32 GT/s CC) | TjPCle_5.0 |  | 7.5 | 10 | fs RMS | 1, 2 |
| 12 | Additive jitter as per Intel QPI 9.6Gbps | $\mathrm{T}_{\mathrm{j} \text { Q } \mathrm{I}}$ |  | 35 | 45 | fs RMS | 1,2 |
| 13 | Additive RMS jitter in 1 MHz to 20 MHz band | $\mathrm{T}_{\mathrm{L} 1 \mathrm{M} \text { _20M }}$ |  | 49 | 62 | fs RMS | $\begin{aligned} & 1,2(100 \mathrm{MHzz} \\ & \text { clock) } \end{aligned}$ |
|  |  |  |  | 40 | 54 | fs RMS | $\begin{gathered} 1,2(133 \mathrm{MHz} \\ \text { clock }) \end{gathered}$ |
| 14 | Additive RMS jitter in 12 kHz to 20 MHz band | $\mathrm{T}_{\mathrm{L} 12 \mathrm{k} \text { _20M }}$ |  | 52 | 65 | fs RMS | $\begin{aligned} & 1,2(100 \mathrm{MHzz} \\ & \text { clock) } \end{aligned}$ |
|  |  |  |  | 42 | 56 | fs RMS | $\begin{gathered} 1,2(133 \mathrm{MHz} \\ \text { clock }) \end{gathered}$ |
| 15 | Noise floor | $\mathrm{N}_{\mathrm{F}}$ |  | -164 | -163 | $\mathrm{dBc} / \mathrm{Hz}$ | $\begin{aligned} & 1,2(100 \mathrm{MHz} \\ & \text { clock) } \end{aligned}$ |
|  |  |  |  | -163 | -162 | $\mathrm{dBc} / \mathrm{Hz}$ | $\begin{gathered} 1,2(133 \mathrm{MHz} \\ \text { clock) } \end{gathered}$ |

. Measured into AC test load as per Figure 19.
2. Measured from differential crossing point to differential crossing point.
3. Input-to-output specs refer to the timing between an input edge and the specific output edge created by it.
4. Integrated after the measurement filter. See Intel DB2000Q specification Jitter Measurement section for the measurement filter details.


Figure 19. AC Test Load as per DB2000Q Specification

Table 18 Differential Output Clock AC Characteristics

|  | Parameter | Symbol | Min. | Typ. | Max. | Units | Notes |
| :---: | :--- | :--- | :--- | :--- | :--- | :--- | :---: |
| 1 | Clock Stabilization Time from PWRGD | Tstab |  |  | 0.1 | ms | 4 |
| 2 | Edge_rate at Vcross | Edge_rate | 2.75 |  | 5 | V/ns | 1 |
| 3 | Slew rate at Vcross | Rise/Fall_Matching |  |  | $5 \%$ | V | 1 |

1. Measured into Figure 19 AC test load.

Table 19 Differential Input Clock AC Characteristics

|  | Parameter | Symbol | Min. | Typ. | Max. | Units | Notes |
| :---: | :--- | :--- | :--- | :--- | :--- | :--- | :--- |
| 1 | Edge_rate | Input_Slew_Rate | 0.7 |  |  | V/ns |  |
| 2 | Total Variation of Vcross Over All Edges | Total_ $\Delta$ _Vcross |  |  | 140 | mV |  |
| 3 | Input Voltage | Input_Voltage | 200 |  |  | mv diff |  |

Table 20 Current Consumption

|  | Parameter | Parameter Condition | Symbol | Min. | Typ. | Max | Units | Notes |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| 1 | Active Mode Supply Current | $\mathrm{fIN}=100 \mathrm{MHz}$ <br> All CK_xP/N outputs enabled | IdDPG |  | 196 | 210 | mA | 1,2 |
| 2 |  | $\mathrm{fIN}=100 \mathrm{MHz}$ <br> All CK_xP/N outputs disabled |  |  | 46 | 50 |  | 1,3 |
| 3 |  | $\mathrm{fIN}=133 \mathrm{MHz}$ <br> All CK_xP/N outputs enabled |  |  | 203 | 220 |  | 1,2 |
| 4 |  | $\begin{aligned} & \text { fIN }=133 \mathrm{MHz} \\ & \text { All CK_xP/N outputs disabled } \end{aligned}$ |  |  | 46 | 51 |  | 1,3 |
| 5 | Power Down Mode Supply Current | $\mathrm{fIN}=100 \mathrm{MHz}$ | IdDPD |  | 21 | 25 | mA | 1,4 |
| 6 |  | $\mathrm{fIN}=133 \mathrm{MHz}$ |  |  | 22 | 26 |  | 1,4 |

1. $\mathrm{VDD}=3.3 \mathrm{~V}+5 \%$
2. Device operating in active mode (Pin PWRGD/PWRDN_N $=1$ ) with all $20 \mathrm{CK} \_x P / \mathrm{N}$ outputs enabled (all OE_xN pin $=0$, all OCR1, OCR2, OCR3 register OEx bits = 1)
3. Device operating in active mode (Pin PWRGD/PWRDN_N=1) with all 20 CK_xP/N outputs disabled (all OCR1, OCR2, OCR3 register OEx bits $=0$ )
4. Device operating in low power mode (Pin PWRGD/PWRDN_N=0)

## SMBus Electrical Characteristics

Table 21 SMBus Electrical Characteristics

|  | Parameter | Symbol | Min. | Typ. | Max | Units | Notes |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| 1 | Nominal Bus Voltage | $\mathrm{VDD}_{\text {smв }}$ | 2.7 |  | 5.5 | V | 1 |
| 2 | Input Low Voltage | $\mathrm{V}_{\mathrm{LL}}$ |  |  | 0.8 | V |  |
| 3 | Input High Voltage | $\mathrm{V}_{1+}$ | 2.1 |  | $\mathrm{VDD}_{\text {smb }}$ | V |  |
| 4 | Output Low Voltage | VoL |  |  | 0.4 | V | At I PuLLup,MAX $^{2}$ |
| 5 | Input Leakage Current | ILEak |  |  | $\pm 10$ | $\mu \mathrm{A}$ |  |
| 6 | Current sinking at $\mathrm{V}_{\mathrm{OL}, \text { max }}$ | IpuLLup | 4 |  |  | mA |  |
| 7 | Pin capacitive load | $\mathrm{C}_{1}$ |  |  | 12 | pF |  |
| 8 | Signal noise immunity from 10 MHz to 100 MHz | $\mathrm{V}_{\text {NoISE }}$ | 300 |  |  | $\mathrm{mV}_{\text {p-p }}$ |  |
| 9 | Noise spike suppression time | TspIKE | 0 |  | 50 | ns | 3 |
| 10 | SMBus Operating Frequency | $\mathrm{F}_{\text {smb }}$ | 10 |  | 400 | kHz |  |
| 11 | Bus free time between Stop and Start Condition | Tbuf | 4.7 |  |  | $\mu \mathrm{s}$ |  |
| 12 | Hold time after (Repeated) Start Condition. After this period, the first clock is generated. | Thd:sta | 4.0 |  |  | $\mu \mathrm{s}$ |  |
| 13 | Repeated Start Condition setup time | Tsu:sta | 4.7 |  |  | $\mu \mathrm{s}$ |  |
| 14 | Stop Condition setup time | T su:sto | 4.0 |  |  | $\mu \mathrm{s}$ |  |
| 15 | Data hold time | Thd:dat | 300 |  |  | ns |  |
| 16 | Data setup time | Tsu:dat | 250 |  |  | ns |  |
| 17 | Clock low period | TLow | 4.7 |  |  | $\mu \mathrm{s}$ |  |
| 18 | Clock high period | TнIGн | 4.0 |  | 50 | $\mu \mathrm{s}$ |  |
| 19 | Clock/Data Fall Time | $\mathrm{T}_{\mathrm{F}}$ |  |  | 300 | ns | 2 |
| 20 | Clock/Data Rise Time | TR |  |  | 1000 | ns | 2 |

1. 3 V to $5 \mathrm{~V} \pm 10 \%$
2. Rise and fall time is defined as follows

TR $=($ VIL,MAX -0.15$)$ to $(\mathrm{VIH}, \mathrm{MIN}+0.15)$
$\mathrm{TF}=(\mathrm{VIH}, \mathrm{MIN}+0.15)$ to (VIL,MAX -0.15 )
3. Devices must provide a means to reject noise spikes of a duration up to the maximum specified value.


Figure 20. SMBus Timing

Table 22 10x10mm QFN Package Thermal Properties

| Parameter | Symbol | Conditions | Value | Units |
| :---: | :---: | :---: | :---: | :---: |
| Maximum Ambient Temperature | $\mathrm{T}_{\mathrm{A}}$ |  | 85 | ${ }^{\circ} \mathrm{C}$ |
| Maximum Junction Temperature | TJMAX |  | 125 | ${ }^{\circ} \mathrm{C}$ |
| Junction to Ambient Thermal Resistance ${ }^{(1)}$ (Note 1) | $\theta_{\text {JA }}$ | still air | 22.6 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
|  |  | $1 \mathrm{~m} / \mathrm{s}$ airflow | 18.7 |  |
|  |  | $2.5 \mathrm{~m} / \mathrm{s}$ airflow | 16.9 |  |
| Junction to Board Thermal Resistance | $\theta_{\text {JB }}$ |  | 9.7 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| Junction to Case Thermal Resistance | $\theta_{\mathrm{Jc}}$ |  | 12.4 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| Junction to Pad Thermal Resistance ${ }^{(2)}$ | $\theta \mathrm{JP}$ | Still air | 5.1 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| Junction to Top-Center Thermal Characterization Parameter | $\psi_{J T}$ | Still air | 0.4 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |

(1) Theta-JA $\left(\theta_{\mathrm{JA}}\right)$ is the thermal resistance from junction to ambient when the package is mounted on a 4-layer JEDEC standard test board and dissipating maximum power
(2) Theta-JP $\left(\theta_{\mathrm{JP}}\right)$ is the thermal resistance from junction to the center exposed pad on the bottom of the package)

## Package Outline



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